

RoHS Recast Compliant

Industrial Micro SD 3.0

Product Specifications

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Version 1.4



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FEATURES:

- **Fully compatible with SD Card Association specifications**
 - Part 1, Physical Layer Specification, Version 3.1 Final
 - Part 3, Security Specification, Version 3.0 Final
- **Capacity range**
 - 4, 8, 16, 32 GB
- **Performance***
 - Sustained Read: Up to 19 MB/sec
 - Sustained Write: Up to 12 MB/sec
- **SD-protocol compatible**
- **Supports SD SPI mode**
- **Backward compatible with 2.0**
- **NAND Flash Type: MLC**
- **Operating frequency: up to 100 MHz**
- **Intelligent endurance design**
 - Built-in advanced ECC algorithm
 - Wear-leveling
 - Flash bad-block management
 - Built in write protect
- **Temperature ranges**
 - Operating temperature:
Commercial: -25°C ~ +85°C
Extended: -40°C ~ +85°C
 - Storage temperature: -40°C ~ +85°C
- **Operating voltage: 2.7V ~ 3.6V**
- **Power consumption***
 - Operating: 47 mA
 - Standby: 150 µA
- **Physical dimension : 15 mm(L) x 11 mm(W) x 1 mm(H)**
- **RoHS Recast Compliant (2011/65/EU)**

*Vary from capacities. Performance values presented here are typical and may vary depending on settings and platforms.

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1. General Description

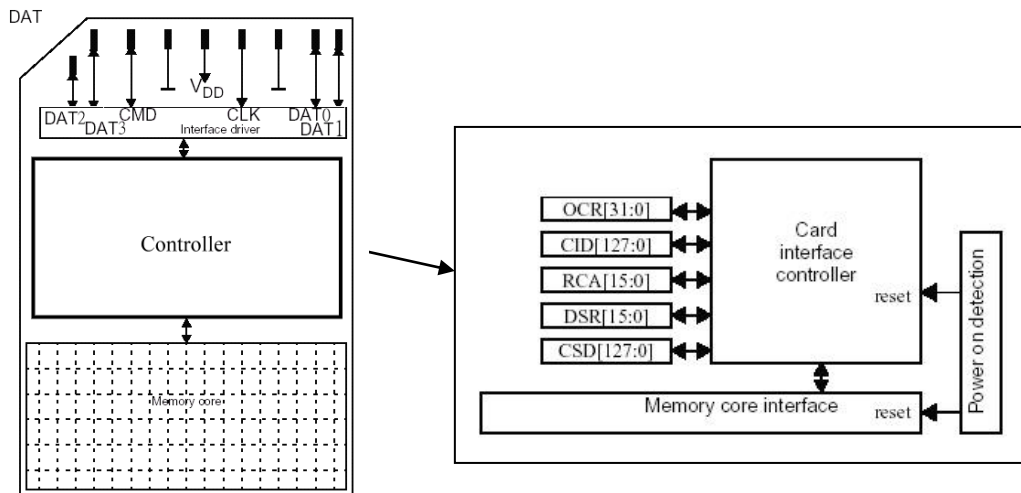
As the demand of reliable and high-performance data storage in a small form factor increases, Apacer's Micro SD card 3.0 is designed specifically for multiple applications by offering high endurance, reliability, and agility, where extreme flexibility, endurance, data integrity, and exceptionally transmission are required.

The Micro SD 3.0 card fully complies with SD Card Association standard. The Command List is compatible with [Part 1 Physical Layer Specification Ver3.1 Final] definitions, while the Card Capacity of Non-secure Area, Secure Area supports [Part 3 Security Specification Ver3.0 Final] Specifications. The card allows selection of either SD or SPI mode for compatibility in data communication. To provide higher transfer rate, the card can extend to 100MHz clock frequency.

The card also comes with endurance features for data error detection and correction, write protection, and password protection.

1.1 Product Function Block

The Micro SD contains a card controller and a memory core for the SD standard interface.



1.2 Functional description

The Micro SD device contains a high level, intelligent flash management that provides many capabilities including:

- High performance flash memory control
- ECC algorithms
- Wear leveling
- Power management

1.2.1 Flash Management

The SD controller contains logic/physical flash block mapping and bad block management system. It will manage all flash block including user data space and spare block.

The Micro SD also contains a sophisticated defect and error management system. It does a read after write under margin conditions to verify that the data is written correctly (except in the case of write pre-erased sectors). In case that a bit is found to be defective, the SD will replace this bad bit with a spare bit within the sector header. If necessary, the Micro SD will even replace the entire sector with a spare sector. This is completely transparent to the master (host device) and does not consume any user data space.

1.2.2 Powerful ECC Algorithms

The powerful ECC algorithms will enhance flash block use rate and whole device life. The SD controller supports up to 68bits ECC circuits to protect data transfer.

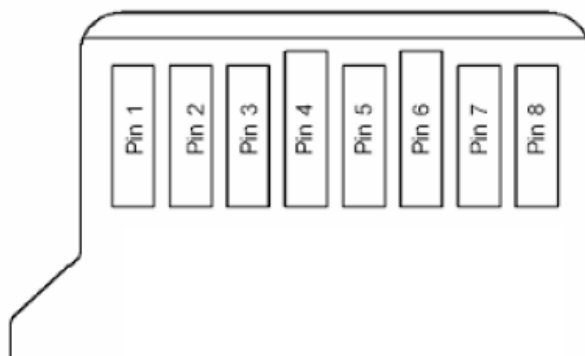
1.2.3 Power Management

A power saving feature of the Micro SD is automatic entrance and exit from sleep mode. Upon completion of an operation, the SD will enter the sleep mode to conserve power if no further commands are received within X seconds, where X is programmable by software. The master does not have to take any action for this to occur. The SD is in sleep mode except when the host is accessing it, thus conserving power.

Any command issued by the master to the Micro SD will cause it to exit sleep mode and response to the master.

2. Electrical characteristics

2.1 Card Architecture



2.2 Pin Assignment

Pin	SD Mode		SPI Mode	
	Name	Description	Name	Description
1	DAT2	Data line[bit 2]	Reserved	
2	CD/DAT3 ²	Card Detect/Data line [bit 3]	CS	Chip select
3	CMD	Command/Response	DI	Data in
4	VDD	Supply voltage	VDD	Supply voltage
5	CLK	Clock	SCLK	Clock
6	VSS	Supply voltage ground	VSS	Supply voltage ground
7	DAT0	Data line[bit 0]	DO	Data out
8	DAT1	Data line[bit 1]	Reserved	

2.3 Capacity Specification

The following table shows the specific capacity for the SD 3.0 card.

Capacity	Total Bytes
4 GB	3,972,005,888
8 GB	7,960,788,992
16 GB	15,997,075,456
32 GB	32,078,036,992

Note: total bytes are viewed under Windows operating system and were measured by SD format too.

2.4 Performance Specification

Performances of the SD 3.0 card are shown in the table below.

Capacity	4 GB	8 GB	16 GB	32 GB
Modes				
Read (MB/s)	19	19	19	19
Write (MB/s)	12	12	12	12

Note: results may vary depending on settings and platforms.

2.5 Electrical Specification

Operating Voltages

Symbol	Parameter	Min.	Max.	Unit
V _{DD}	Power Supply Voltage	2.7	3.6	V

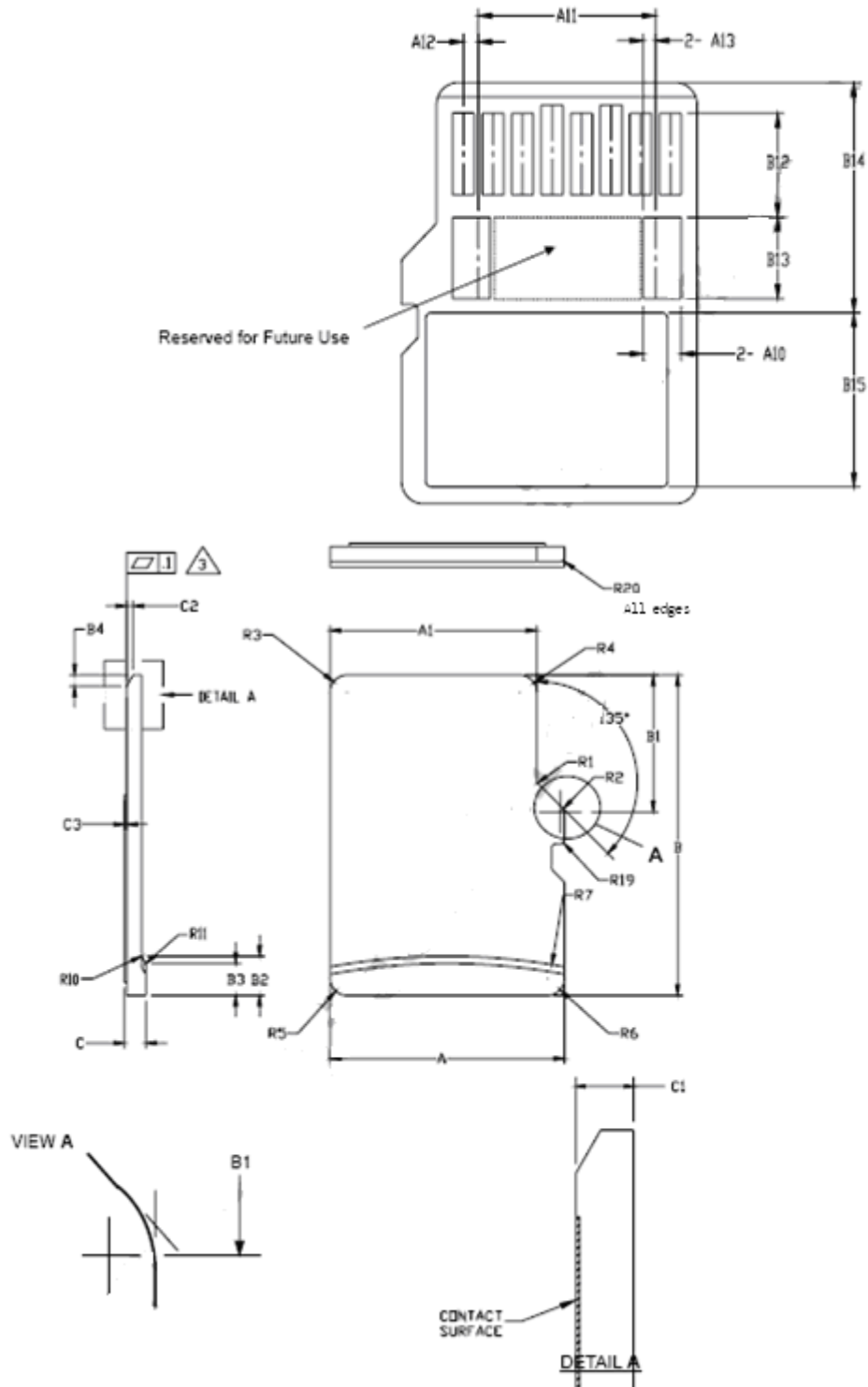
Power consumption

Capacity	4 GB	8 GB	16 GB	32 GB
Modes				
Operating (mA)	40	42	45	47
Standby (μA)	100	100	100	150

Note: results may vary depending on settings and platforms.

3. Physical Characteristics

3.1 Physical Dimension



COMMON DIMENSIONS				NOTE
SYMBOL	MIN	NOM	MAX	
A	10.90	11.00	11.10	
A1	9.60	9.70	9.80	
A2	-	3.85	-	BASIC
A3	7.60	7.70	7.80	
A4	-	1.10	-	BASIC
A5	0.75	0.80	0.85	
A6	-	-	8.50	
A7	0.90	-	-	
A8	0.60	0.70	0.80	
A9	0.80	-	-	
A10	1.35	1.40	1.45	
A11	6.50	6.60	6.70	
A12	0.50	0.55	0.60	
A13	0.40	0.45	0.50	
B	14.90	15.00	15.10	
B1	6.30	6.40	6.50	
B2	1.64	1.84	2.04	
B3	1.30	1.50	1.70	
B4	0.42	0.52	0.62	
B5	2.80	2.90	3.00	
B6	5.50	-	-	
B7	0.20	0.30	0.40	
B8	1.00	1.10	1.20	
B9	-	-	9.00	
B10	7.80	7.90	8.00	
B11	1.10	1.20	1.30	
B12	3.60	3.70	3.80	
B13	2.80	2.90	3.00	
B14	8.20	-	-	
B15	-	-	6.20	
C	0.90	1.00	1.10	
C1	0.60	0.70	0.80	
C2	0.20	0.30	0.40	
C3	0.00	-	0.15	
D1	1.00	-	-	
D2	1.00	-	-	
D3	1.00	-	-	
R1	0.20	0.40	0.60	
R2	0.20	0.40	0.60	
R3	0.70	0.80	0.90	
R4	0.70	0.80	0.90	
R5	0.70	0.80	0.90	
R6	0.70	0.80	0.90	
R7	29.50	30.00	30.50	
R10	-	0.20	-	
R11	-	0.20	-	
R17	0.10	0.20	0.30	
R18	0.20	0.40	0.60	
R19	0.05	-	0.20	
R20	0.02	-	0.15	

Notes:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

2. DIMENSIONS ARE IN MILLIMETERS.

3. COPLANARITY IS ADDITIVE TO C1 MAX THICKNESS.

3.2 Environmental Specifications

3.2.1 Climatic Testing

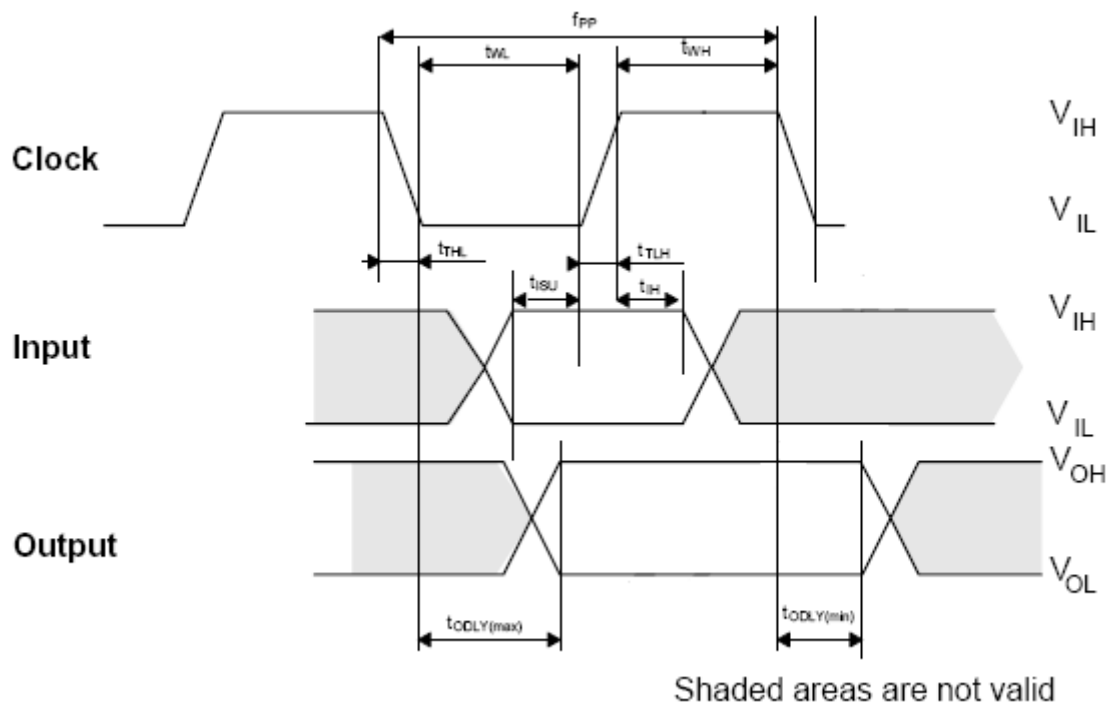
Test Item	DUT State	Test Condition	
		Temperature	Duration
High Temperature	Storage	85°C	500 Hours
Low Temperature	Storage	- 40°C	500 Hours
Temperature & Humidity	Storage	55°C 95%RH	500 Hours
Temperature Cycling	Storage	- 40°C ~ 85°C 30min hold each	50 Cycles

3.2.2 Durability Testing

Test Item	Descriptions
Insertion/Removal	10,000 cycles
Bending	10nt/5 times for 6 faces and 4 corners (each drop was performed 3 times, total of 30 drops)
Electrostatic Discharge	Contact discharge: HCP & VCP Air discharge: ALL – VSS ($\pm$), ALL – VCC ($\pm$) VCC – VSS ($\pm$), ALL – ALL ($\pm$)
Ultraviolet Radiation	Units are non-operating. UVB bandwidth : 313 nm. Test irradiation : 0.63 w/m ² /nm. Radiation cycle : Radiation on for 4 hours at temperature 60°C, then radiation off for 4 hours at temperature 60°C. Number of cycle : 6 cycles. Duration of test : 48 hours
Drop	1.5 m free fall, 10 times
Salt Water Spray	3+/-1%NaCl; 35°C; 24hrs
Torque	0.1 N-m or $\pm$ 2.5 degree 5 time; 30 sec/direction

4. AC Characteristics

4.1 Micro SD Interface Timing (Default)

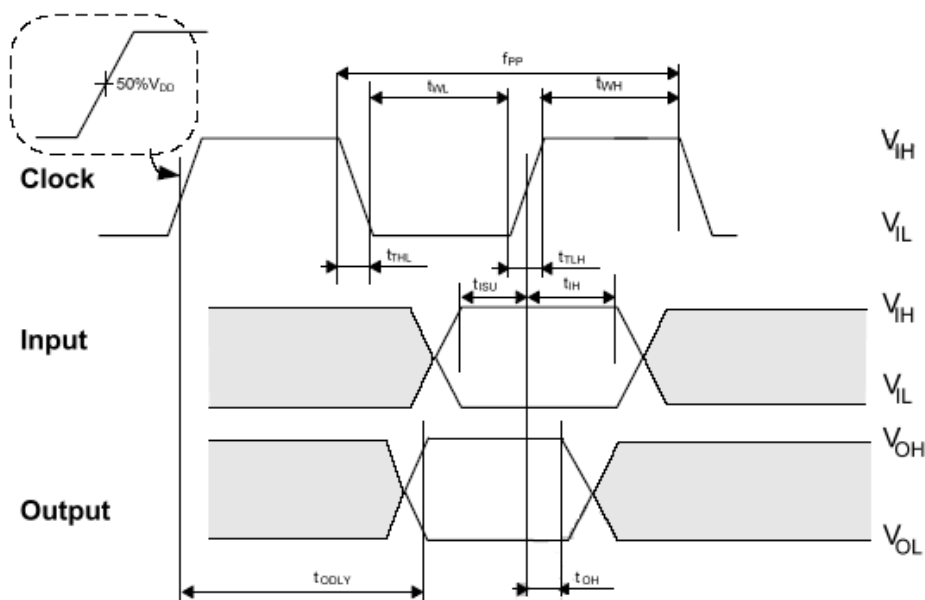


SYMBOL	PARAMETER	MIN	MAX	UNIT	Note
Clock CLK (All values are referred to min(V_{IH}) and max(V_{IL}))					
f _{PP}	Clock frequency Data Transfer Mode	0	25	MHz	C _{card} ≤ 10 pF (1 card)
f _{OD}	Clock frequency Identification Mode	0 ₍₁₎ /100	400	kHz	C _{card} ≤ 10 pF (1 card)
t _{WL}	Clock low time	10	-	ns	C _{card} ≤ 10 pF (1 card)
t _{WH}	Clock high time	10	-	ns	C _{card} ≤ 10 pF (1 card)
t _{TLH}	Clock rise time	-	10	ns	C _{card} ≤ 10 pF (1 card)
t _{THL}	Clock fall time	-	10	ns	C _{card} ≤ 10 pF (1 card)
t _{ISU}	Input setup time	5	-	ns	C _{card} ≤ 10 pF (1 card)
t _{IH}	Input hold time	5	-	ns	C _{card} ≤ 10 pF (1 card)

t_{ODLY}	Output delay time	0	14	ns	$C_L \leq 40$ pF (1 card)
t_{ODLY}	Output Delay time during Identification Mode	0	50	ns	$C_L \leq 40$ pF (1 card)

(1)0Hz means to stop the clock. The given minimum frequency range is for cases that requires the clock to be continued.

4.2 Micro SD Interface Timing (High Speed Mode)



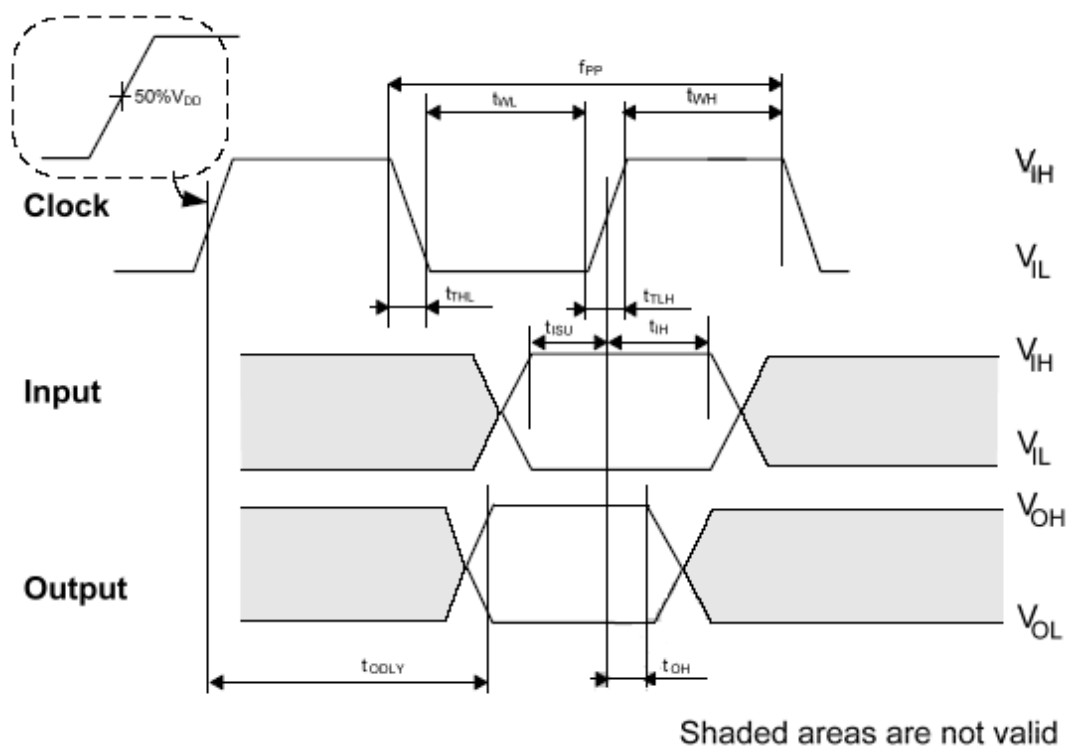
Shaded areas are not valid

SYMBOL	PARAMETER	MIN	MAX	UNIT	Note
f_{PP}	Clock frequency data transfer mode	0	50	MHz	$C_{card} \leq 10$ pF (1 card)
t_{WL}	Clock low time	7	-	ns	$C_{card} \leq 10$ pF (1 card)
t_{WH}	Clock high time	7	-	ns	$C_{card} \leq 10$ pF (1 card)
t_{TLH}	Clock rise time	-	3	ns	$C_{card} \leq 10$ pF (1 card)
t_{THL}	Clock fall time	-	3	ns	$C_{card} \leq 10$ pF (1 card)
t_{ISU}	Input setup time	6	-	ns	$C_{card} \leq 10$ pF (1 card)
t_{IH}	Input hold time	2	-	ns	$C_{card} \leq 10$ pF (1 card)
t_{ODLY}	Output delay time		14	ns	$C_L \leq 40$ pF (1 card)
t_{OH}	Output hold time	2.5	50	ns	$C_L \leq 15$ pF (1 card)
C_L	System capacitance of each line*		40	pF	$C_L \leq 15$ pF (1 card)

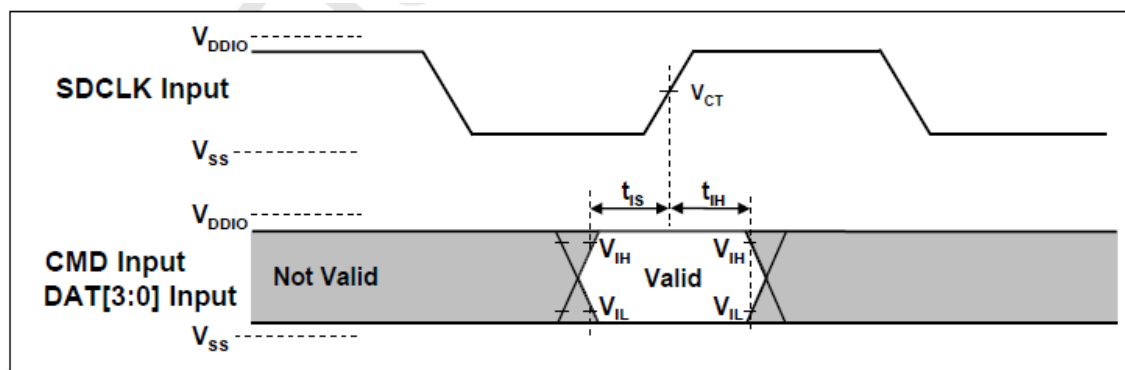
*In order to satisfy severe timing, host shall run on only one card

4.3 SD Interface Timing (SDR12, SDR25 and SDR50 Modes) Input

Symbol	Min	Max	Unit	Remark
t_{CLK}	4.80	-	ns	208MHz (Max.), Between rising edge, $V_{CT}=0.975V$
t_{CR}, t_{CF}	-	$0.2 \cdot t_{CLK}$	ns	$t_{CR}, t_{CF} < 2.00ns$ (max.) at 100MHz, CCARD=10pF
Clock Duty	30	70	%	



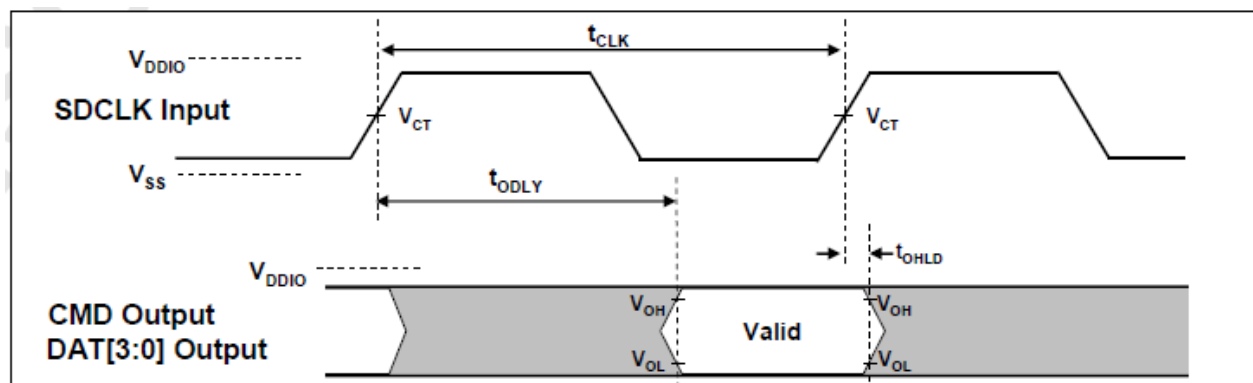
4.3.1 SDR50 Input Timing



Card Input Timing

Symbol	Min	Max	Unit	SDR50 Mode
t_{IS}	3.00	-	ns	CCARD =10pF, VCT= 0.975V
t_{IH}	0.80	-	ns	CCARD =5pF, VCT= 0.975V

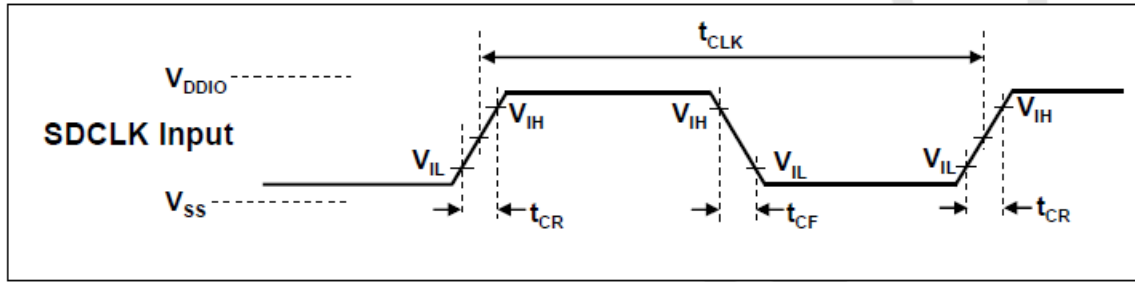
4.3.2 Output



Output Timing of Fixed Data Window

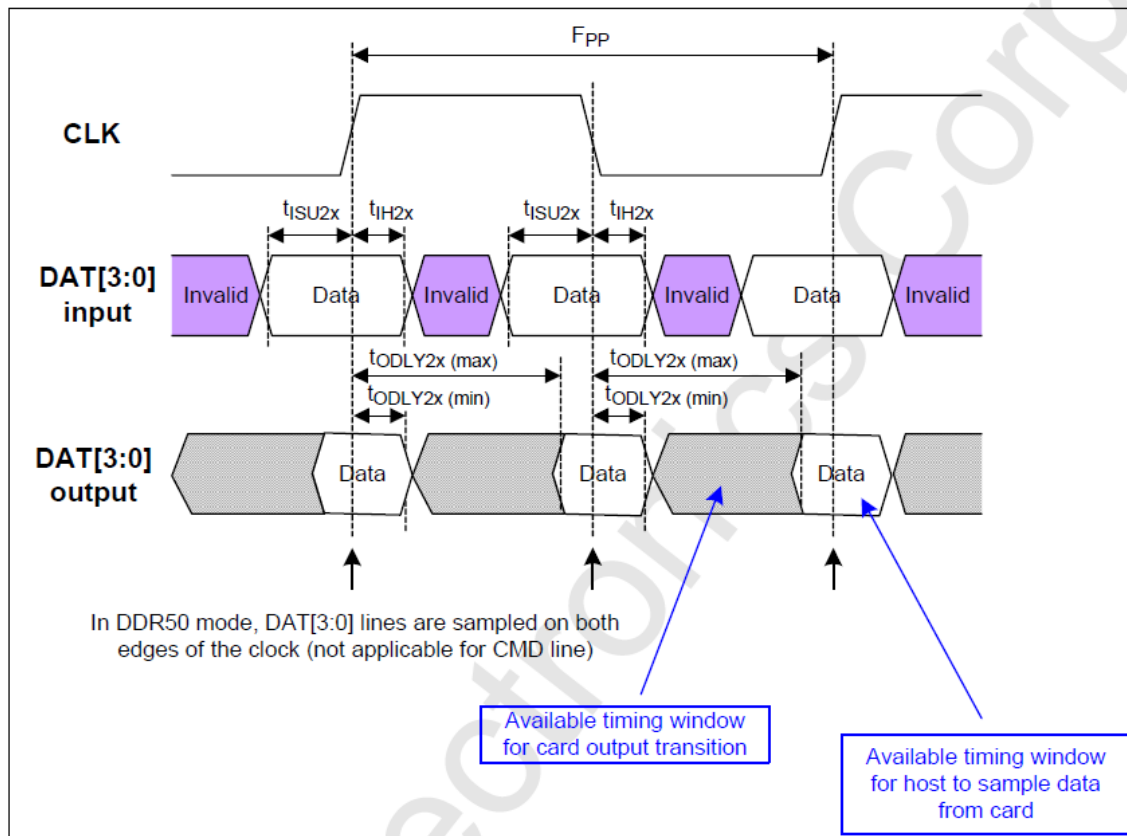
Symbol	Min	Max	Unit	Remark
t_{ODLY}	-	7.5	ns	$t_{CLK} \geq 10.0ns$, CL=30pF, using driver Type B, for SDR50
t_{ODLY}	-	14	ns	$t_{CLK} \geq 20.0ns$, CL=40pF, using driver Type B, for SDR25 and SDR12,
T_{OH}	1.5	-	ns	Hold time at the t_{ODLY} (min.), CL=15pF

4.3.3 SD Interface Timing (DDR50 Mode)



Clock Signal Timing

Symbol	Min	Max	Unit	Remark
t_{CLK}	20	-	ns	50MHz (Max.), Between rising edge
t_{CR}, t_{CF}	-	$0.2 \cdot t_{CLK}$	ns	$t_{CR}, t_{CF} < 4.00\text{ns (max.)}$ at 50MHz, CCARD=10pF
Clock Duty	45	55	%	



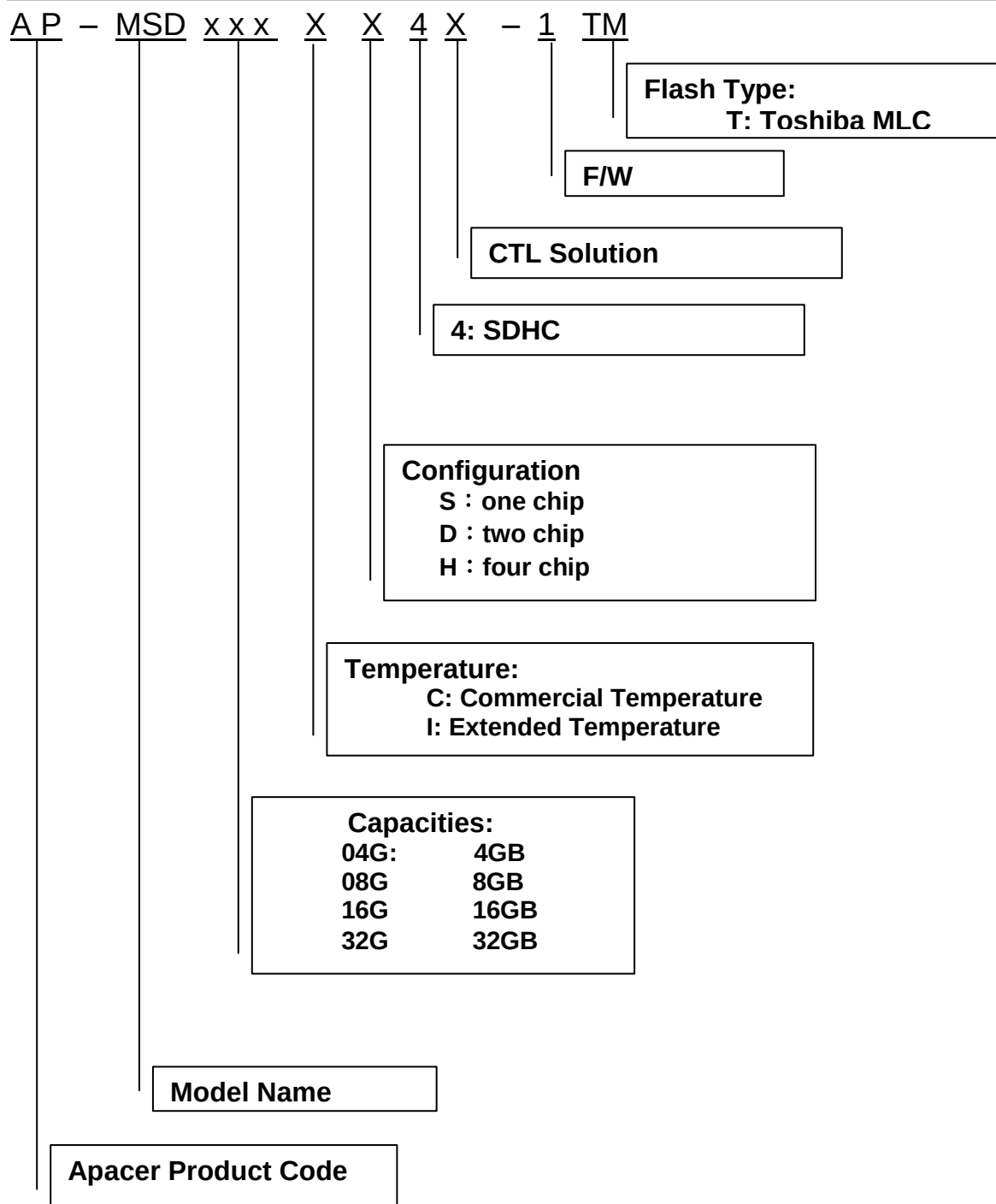
Timing Diagram DAT Inputs/Outputs Referenced to CLK in DDR50 Mode

4.3.4 Bus Timings – Parameters Values (DDR50 Mode)

Symbol	Parameters	Min	Max	Unit	Remark
Input CMD (referenced to CLK rising edge)					
t_{ISU}	Input set-up time	6	-	ns	$C_{card} \leq 10$ pF (1 card)
t_{IH}	Input hold time	0.8	-	ns	$C_{card} \leq 10$ pF (1 card)
Output CMD (referenced to CLK rising edge)					
t_{ODLY}	Output Delay time during Data Transfer Mode	-	13.7	ns	$C_L \leq 30$ pF (1 card)
T_{OH}	Output Hold time	1.5	-	ns	$C_L \geq 15$ pF (1 card)
Inputs DAT (referenced to CLK rising and falling edges)					
t_{ISU2x}	Input set-up time	3	-	ns	$C_{card} \leq 10$ pF (1 card)
t_{IH2x}	Input hold time	0.8	-	ns	$C_{card} \leq 10$ pF (1 card)
Outputs DAT (referenced to CLK rising and falling edges)					
t_{ODLY2x}	Output Delay time during Data Transfer Mode	-	7.0	ns	$C_L \leq 25$ pF (1 card)
T_{OH2x}	Output Hold time	1.5	-	ns	$C_L \geq 15$ pF (1 card)

5. Product Ordering Information

5.1 Product Code Designations



5.2 Valid Combinations

5.2.1 Commercial Temperature

Capacity	AP/N
4GB	AP-MSD04GCS4P-1TM
8GB	AP-MSD08GCS4P-1TM
16GB	AP-MSD16GCD4P-1TM
32GB	AP-MSD32GCH4P-1TM

5.2.2 Extended Temperature

Capacity	AP/N
4GB	AP-MSD04GIS4P-1TM
8GB	AP-MSD08GIS4P-1TM
16GB	AP-MSD16GID4P-1TM
32GB	AP-MSD32GIH4P-1TM

Note: Please consult with Apacer sales representatives for availabilities.

Revision History

Revision	Description	Date
1.0	Official release	03/01/2013
1.1	Revised operating temperature	03/05/2013
1.2	Added extended temperature specifications	08/12/2014
1.3	Revised part numbers	09/24/2014
1.4	Updated environment specifications	02/09/2015

Global Presence

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